

Photo Resist 제품 리스트

제품에 따라 100, 250, 500m, 1L, 1Gallon 용량 선택 가능하며, 관련 developer, remover를 취급하고 있습니다.

Type	Product	TF (μm) 4000 rpm	Characteristic Properties	Application	Resolution [μm]	Con- trast	Expo- sure	Thinner	Developer	Remover
Positive resist	KL 5302, 5305, 5310, 5315	0.13 – 1.2	0.12-2.5 μm FT, high sensitivity, throughput	ICs	0.55	-	i-line, g-line, BB-UV	-	TMAH	NMP, DMSO
	KL 6003, 6005, 6008	2.5 – 5	2.2-10 μm FT, high sensitivity, throughput	MEMS	2	-		-	TMAH	NMP, DMSO
	K-PRO7, 15	7 – 15 at 1000 rpm	5-25 μm FT, high sensitivity, throughput	Packaging	-	-		-	TMAH, KOH	NMP
	AR-P 1210, 1220, 1230	[0.5 – 10]	spray resist, var. applications	MEMS	1	3		-	300-44	600-71 300-73
	AR-P 3110, 3120, 3170	1.0; 0.6; 0.1	high resolution, adhesion-enhanced	masks, lattices	0.5; 0.4; 0.4	3		300-12	300-35 300-26	300-76 300-73
	AR-P 3210, 3220, 3250	10; 10; 5	thick resist with high dimen. Accuracy up to 100 μm	electro-plating, MST	4; 3; 1.2	2; 2; 2.5		300-12	300-26	600-71 300-76
	AR-P 3510, 3540	2; 1.4	wide process range, high resolution	ICs	0.8; 0.7	4; 4.5		300-12	300-35 300-26	600-71 300-73
	AR-P 3510T, 3540T	2; 1.4	wide process range, high res., developable in 0.26n TMAH	ICs	0.6; 0.5	4.5; 5		300-12	300-44 300-26	600-71 300-76
	AR-P 3740, 3840	1.4; 1.4	highest resolution, sub- μm, high contrast, 3840 dyed	VLSIC	0.4; 0.4	6.0; 6.0		300-12	300-47 300-26	600-71 300-76
	AR-P 5320, 5350	5; 1	undercut structure (single layer lift-off)	evaporation structures	2; 0.5	4; 5		300-12	300-26	600-76 300-73
Negative resist	HARE SQ-2, 5, 10, 25, 50	2000 rpm: 2; 5; 10; 25; 50	1-100 μm FT, fully compatible with SU-8	MEMS, microfluidics	1 – 5	4 ~ 6	i-line, NUV, BB-UV	-	SQ developer	-
	KL LO1602, 1604, 1607	1.8 – 4.2	2-9 μm FT, lift-off profile	Lift-off	1.7 – 7	-	i-line, BB-UV	-	TMAH	NMP, DMSO
	APOL-LO 3202, 3204, 3207	2 – 5	2-10 μm FT, high resolution lift-off profile	Lift-off	0.6	-	i-line, BB-UV	-	TMAH	NMP, DMSO
	AR-N 2210, 2220, 2230	[0.5 – 10]	spray resist, var. applications	MEMS	1	3	i-, g-line, BB-UV	-	300-44	600-71 300-73
	AR-N 4340	1.4	highly sensitive, high resolution, CAR	ICs	0.5	5	i-line, g-line	300-12	300-475 300-26	600-76 300-72
	AR-N 4400-50, -25, -10, -05	1000 rpm: 50; 25; 10; 5	thick films up to 100, 50, 20, 10 μm, easy removal	electro-plating, MST, LIGA	5; 3.5; 2; 1	6; 5; 4; 4	i-line, X-ray, e-beam	300-12	300-44 bis -475	600-71 600-70
	AR-N 4450-10	1000 rpm: 10	thick films up to 20 μm, lift-off		2.0; 3.5	10 lift-off		300-12	300-47	600-71 600-70
Special application	KL IR15, IR15 Lift Off	3000 rpm: 1.5	1.2-2.6 μm FT, image reversal, lift-off	ICs, Lift-off	2	-	i-line, g-line, BB-UV	-	TMAH	NMP, DMSO
	AR-U 4030, 4040, 4060	1.8; 1.6; 0.6	optionally pos. or neg., lift-off	ICs	0.8; 0.7; 0.5	3; 3; 3.5		300-12	300-35 300-26	600-72 300-76
	AR-P 5910	5	complicated pattern, up to 5% HF/BOE	MEMS	2	2		300-12	300-26	300-76 300-73
	SurPass	-	Adhesion promoter / Priming Agent through cationic interaction and modification of the substrate surface energy							DI water or IPA
	AR 300-80 HMDS	0.015; 0.005	Adhesion promoter	-	-	-	-	-	-	600-70 600-71

Type	Product	TF (μm) 4000 rpm	Characteristic Properties	Application	Resolution [μm]	Con- trast	Expo- sure	Thinner	Developer	Remover
	AR-PC 503, dyed 504, 5040	1.2; 2.2	protective coating, 40% KOH etch-stable	protective film	-	-	-	600-01	-	600-71 300-76
	AR-BR 5460, 5480	1; 0.5	bottom resist for 2L lift- off	lift-off (pos./neg.)	3; 1.5	lift-off	-	-	-	300-76 300-73